

TOSHIBA Photocoupler GaAs Ired & Photo-Transistor

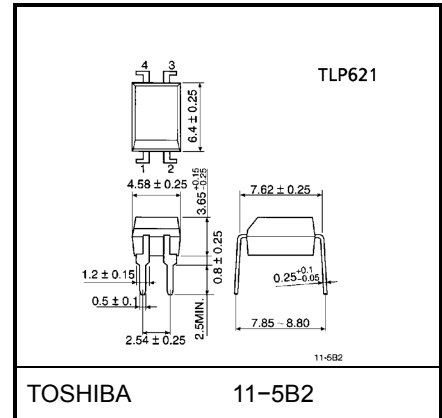
TLP621, TLP621-2, TLP621-4

Programmable Controller
AC / DC-Input Module
Solid State Relay

The TOSHIBA TLP621, -2 and -4 consists of a photo-transistor optically coupled to a gallium arsenide infrared emitting diode. The TLP621-2 offers two isolated channels in an eight lead plastic DIP, which the TLP621-4 provides four isolated channels in a sixteen plastic DIP.

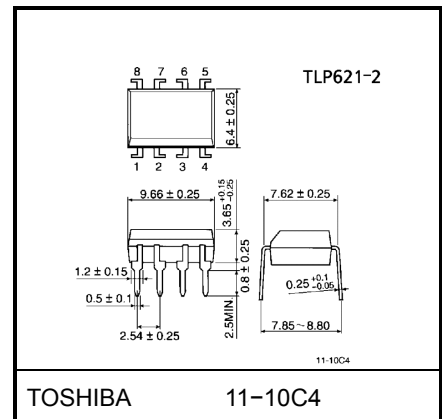
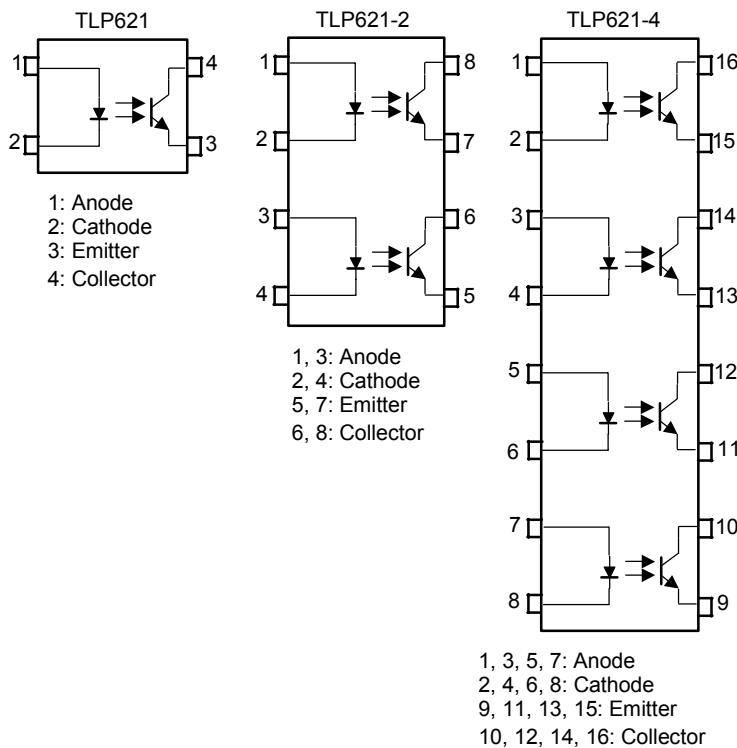
- Collector-emitter voltage: 55 V (min.)
- Current transfer ratio: 50% (min.)
Rank GB: 100% (min.)

Unit in mm

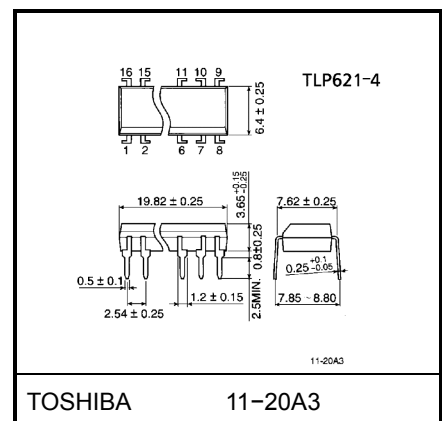


Weight: 0.26 g

Pin Configurations (top view)



Weight: 0.54 g



Weight: 1.1 g

• Current Transfer Ratio

Type	Classi- fication *1	Current Transfer Ratio (%) (I_C / I_F)		Marking Of Classification
		$I_F = 5\text{mA}, V_{CE} = 5\text{V}, T_a = 25^\circ\text{C}$		
		Min.	Max.	
TLP621	(None)	50	600	Blank, Y, Y [■] , G, G [■] , B, B [■] , GB
	Rank Y	50	150	Y, Y [■]
	Rank GR	100	300	G, G [■]
	Rank BL	200	600	B, B [■]
	Rank GB	100	600	G, G [■] , B, B [■] , GB
TLP621-2 TLP621-4	(None)	50	600	Blank, GR, BL, GB
	Rank GB	100	600	GR, BL, GB

*1: Ex. rank GB: TLP621 (GB)

(Note) Application type name for certification test, please use standard product type name, i.e.

TLP621 (GB): TLP621

TLP621-2 (GB): TLP621-2

	Made In Japan		Made In Thailand	
UL recognized	E67349	*2	E152349	*2
BSI approved	6508, 7445	*3	6505, 7445	*3
SEMKO approved	9735090 / 01	*4	—	

*2 UL1577

*3 BS EN60065: 1994, BS EN60950: 1992

*4 EN60950 (approved is TLP621 only)

- Option (D4) type
VDE approved: DIN VDE0884 / 06.92, certificate no. 68384
Maximum operating insulation voltage: 890 V_{PK}
Highest permissible over voltage: 8000 V_{PK}

(Note) When a VIDE0884 approved type is needed, please designate the “Option (D4)”

	7.62 mm pich standard type	10.16 mm pich (LF2) type
• Creepage distance	: 6.4 mm (min.)	8.0 mm (min)
Clearance	: 6.4 mm (min.)	8.0 mm (min)
Insulation thickness	: 0.4 mm (min.)	0.4 mm (min)

Maximum Ratings (Ta = 25°C)

Characteristic	Symbol	Rating		Unit	
		TLP621	TLP621-2 TLP621-4		
LED	Forward current	I _F	60	50	mA
	Forward current derating	ΔI _F /°C	-0.7 (Ta > 39°C)	-0.5 (Ta = 25°C)	mA/°C
	Pulse forward current	I _{FP}	1 (100μs pulse, 100pps)		A
	Power dissipation	P _D	100	70	mW
	Power dissipation derating	ΔP _D /°C	-1.0	-0.7	mW/°C
	Reverse voltage	V _R	5		V
	Junction temperature	T _j	125		°C
Detector	Collector-emitter voltage	V _{CEO}	55		V
	Emitter-collector voltage	V _{ECO}	7		V
	Collector current	I _C	50		mA
	Collector power dissipation (1 circuit)	P _C	150	100	mW
	Collector power dissipation derating (1 circuit, Ta ≥ 25°C)	ΔP _C /°C	-1.5	-1.0	mW/°C
	Junction temperature	T _j	125		°C
Storage temperature range	T _{stg}	-55~125		°C	
Operating temperature range	T _{opr}	-55~100		°C	
Lead soldering temperature	T _{sol}	260 (10 s)		°C	
Total package power dissipation	P _T	250	150	mW	
Total package power dissipation derating (Ta ≥ 25°C)	ΔP _T /°C	-2.5	-1.5	mW/°C	
Isolation voltage (Note 1)	BV _S	5000 (AC, 1min., R.H. ≤ 60%)		V _{rms}	

(Note 1) Device considered a two terminal: LED side pins shorted together, and detector side pins shorted together.

Recommended Operating Conditions

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Supply voltage	V _{CC}	—	5	24	V
Forward current	I _F	—	16	20	mA
Collector current	I _C	—	1	10	mA
Operating temperature	T _{opr}	-25	—	85	°C

Individual Electrical Characteristics (Ta = 25°C)

Characteristic		Symbol	Test Condition	Min.	Typ.	Max.	Unit
LED	Forward voltage	V_F	$I_F = 10 \text{ mA}$	1.0	1.15	1.3	V
	Reverse current	I_R	$V_R = 5 \text{ V}$	—	—	10	μA
	Capacitance	C_T	$V = 0, f = 1 \text{ MHz}$	—	30	—	pF
Detector	Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 0.5 \text{ mA}$	55	—	—	V
	Emitter-collector breakdown voltage	$V_{(BR)ECO}$	$I_E = 0.1 \text{ mA}$	7	—	—	V
	Collector dark current	I_{CEO}	$V_{CE} = 24 \text{ V}$	—	10	100	nA
			$V_{CE} = 24 \text{ V}, T_a = 85^\circ\text{C}$	—	2	50	μA
Capacitance (collector to emitter)	C_{CE}	$V = 0, f = 1 \text{ MHz}$	—	10	—	pF	

Coupled Electrical Characteristics (Ta = 25°C)

Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Current transfer ratio	I_C / I_F	$I_F = 5 \text{ mA}, V_{CE} = 5 \text{ V}$ Rank GB	50	—	600	%
			100	—	600	
Saturated CTR	$I_C / I_F (\text{sat})$	$I_F = 1 \text{ mA}, V_{CE} = 0.4 \text{ V}$ Rank GB	—	60	—	%
			30	—	—	
Collector-emitter saturation voltage	$V_{CE} (\text{sat})$	$I_C = 2.4 \text{ mA}, I_F = 8 \text{ mA}$	—	—	0.4	V
		$I_C = 0.2 \text{ mA}, I_F = 1 \text{ mA}$ Rank GB	—	0.2	—	
			—	—	0.4	

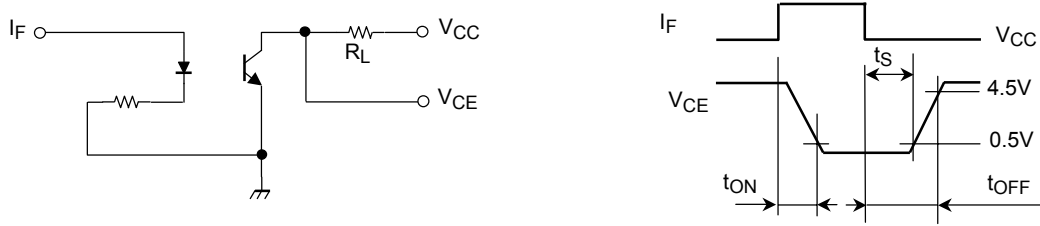
Isolation Characteristics (Ta = 25°C)

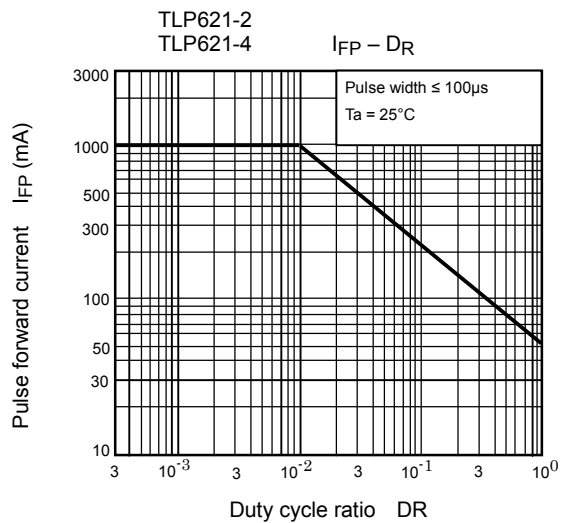
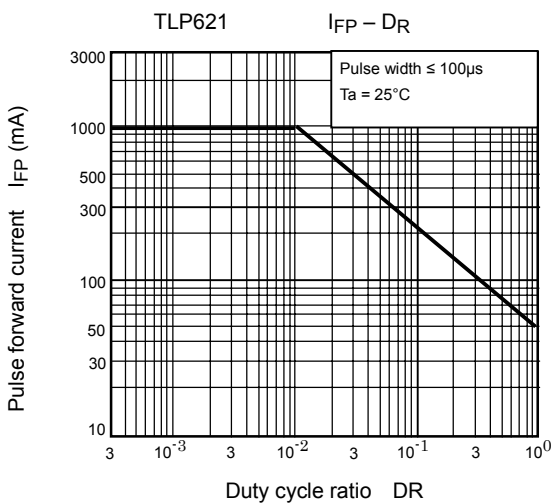
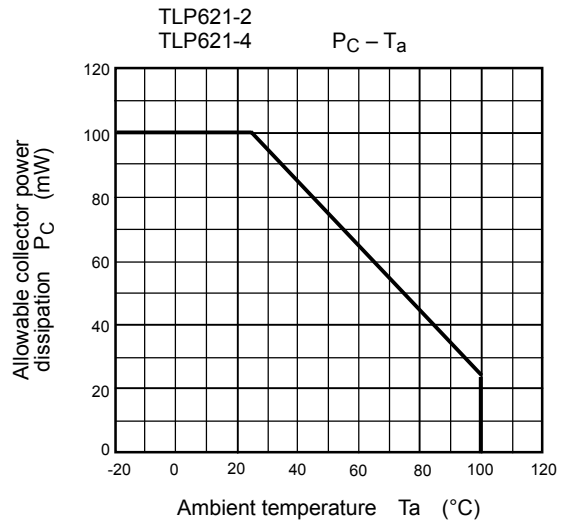
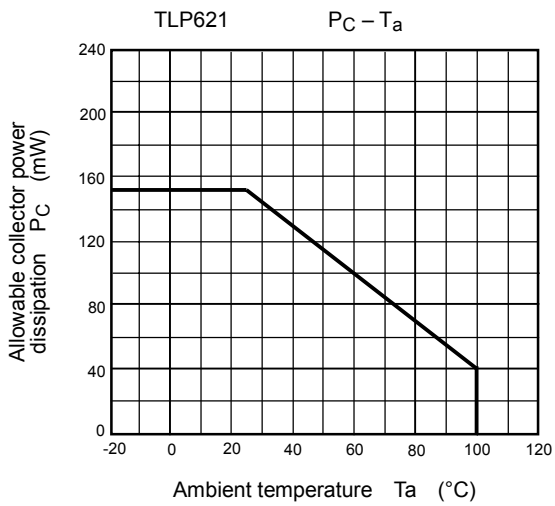
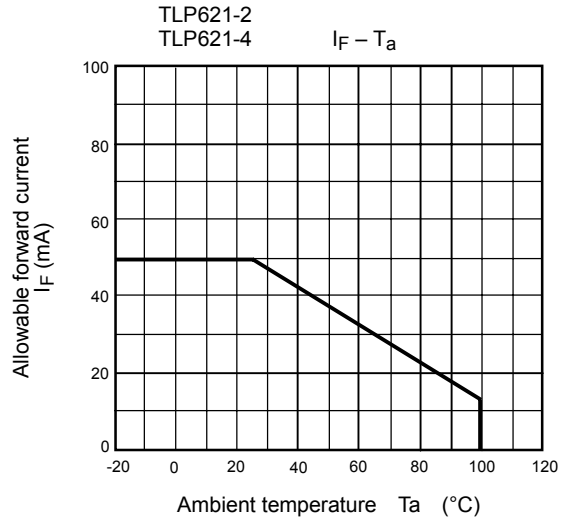
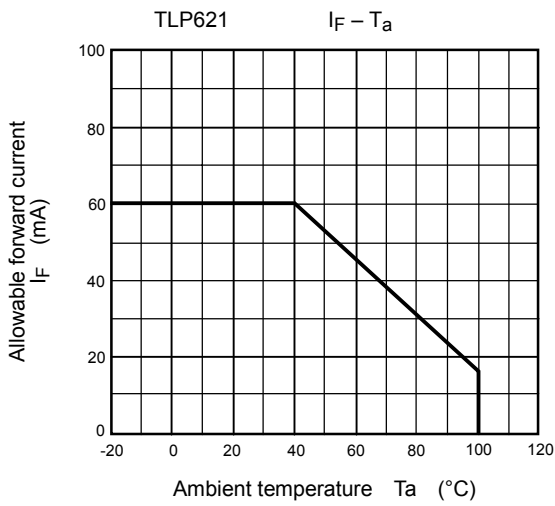
Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Capacitance (input to output)	C_S	$V_S = 0, f = 1 \text{ MHz}$	—	0.8	—	pF
Isolation resistance	R_S	$V_S = 500 \text{ V}$	1×10^{12}	10^{14}	—	Ω
Isolation voltage	BV_S	AC, 1 minute	5000	—	—	V_{rms}
		AC, 1 second, in oil	—	10000	—	V_{dc}
		DC, 1 minute, in oil	—	10000	—	

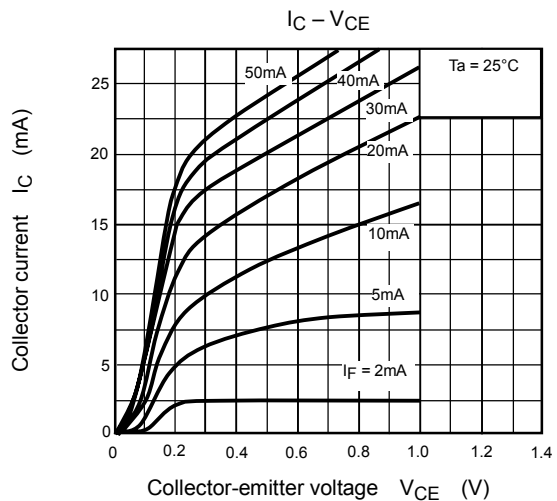
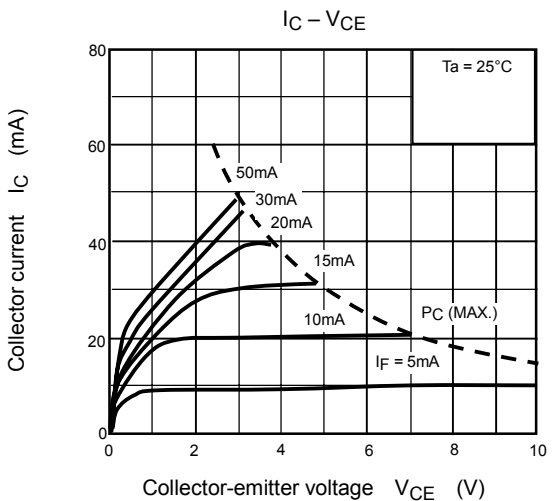
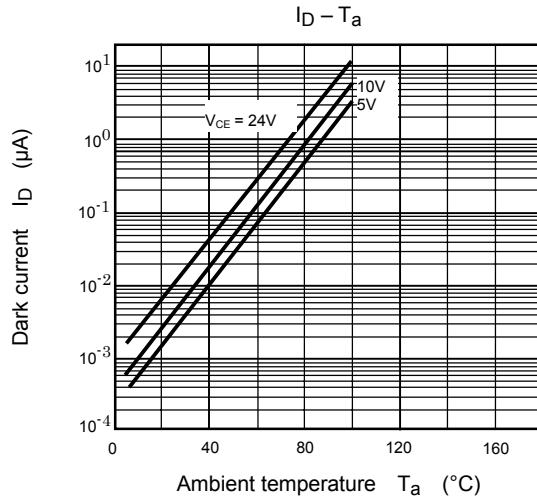
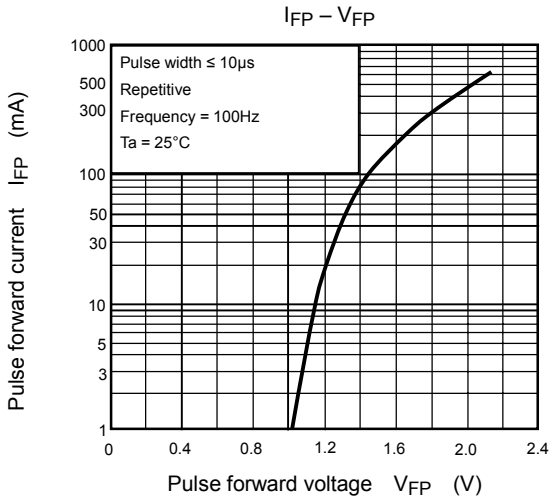
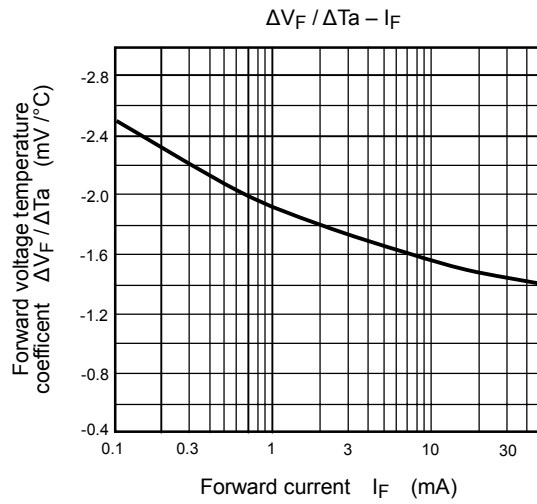
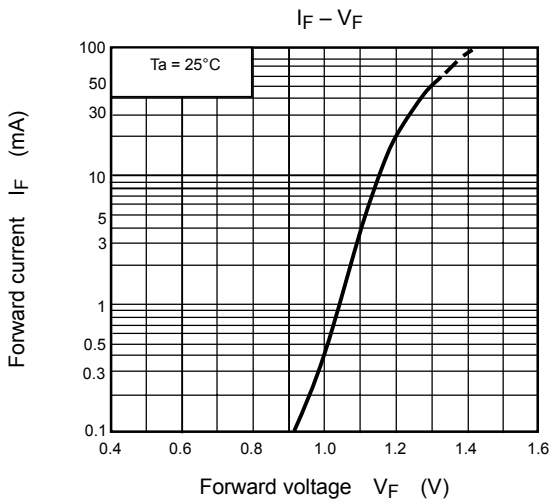
Switching Characteristics (Ta = 25°C)

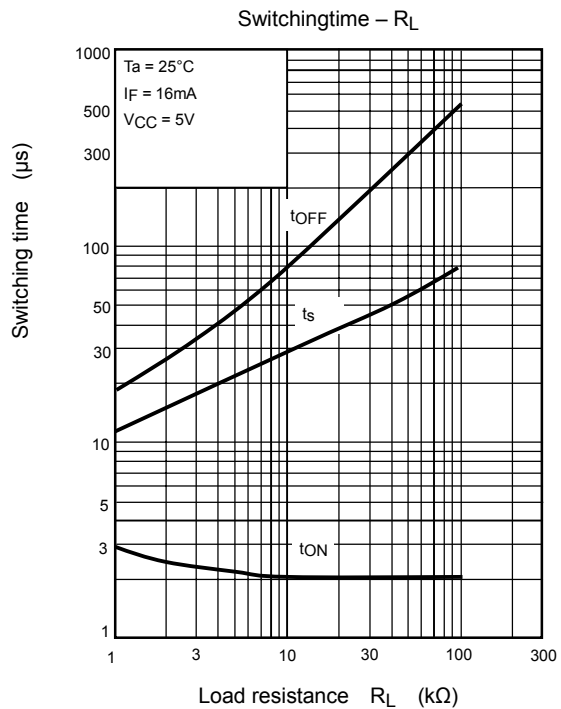
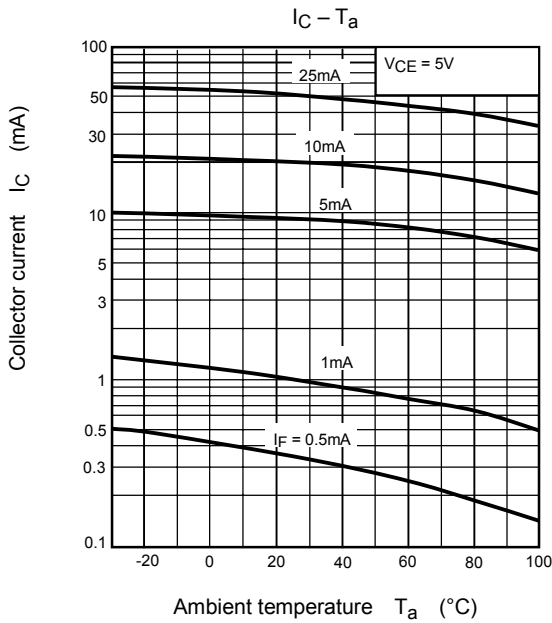
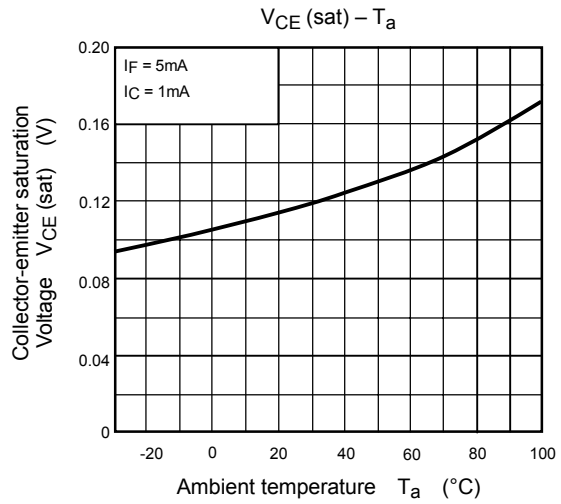
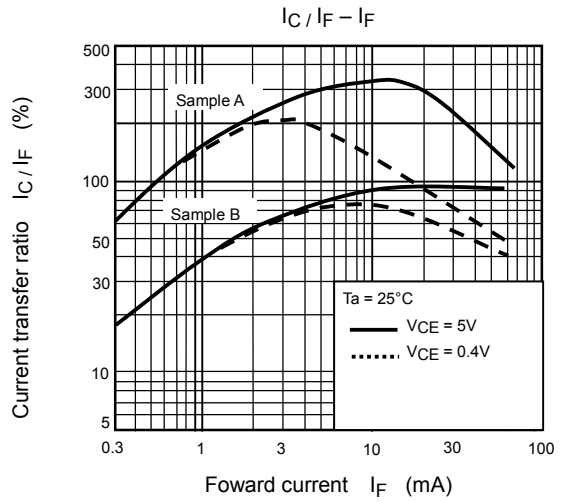
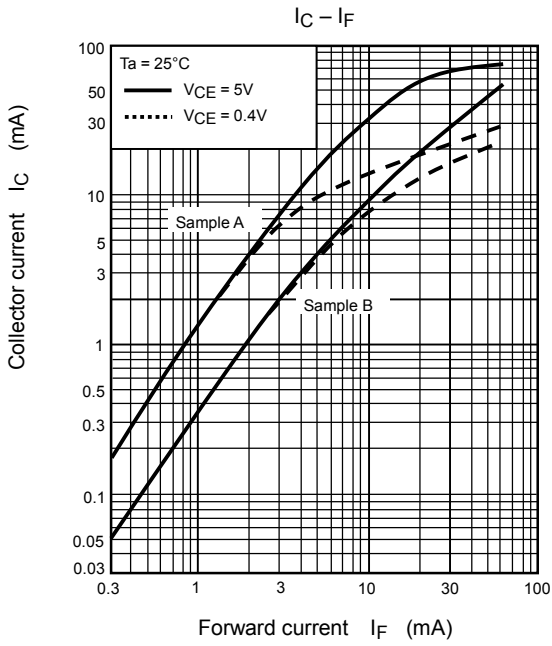
Characteristic	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Rise time	t_r	$V_{CC} = 10\text{ V}, I_C = 2\text{ mA}$ $R_L = 100\Omega$	—	2	—	μs
Fall time	t_f		—	3	—	
Turn-on time	t_{on}		—	3	—	
Turn-off time	t_{off}		—	3	—	
Turn-on time	t_{ON}	$R_L = 1.9\text{ k}\Omega$ (Fig.1) $V_{CC} = 5\text{ V}, I_F = 16\text{ mA}$	—	2	—	μs
Storage time	t_s		—	15	—	
Turn-off time	t_{OFF}		—	25	—	

Fig. 1 Switching time test circuit









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000707EBC

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